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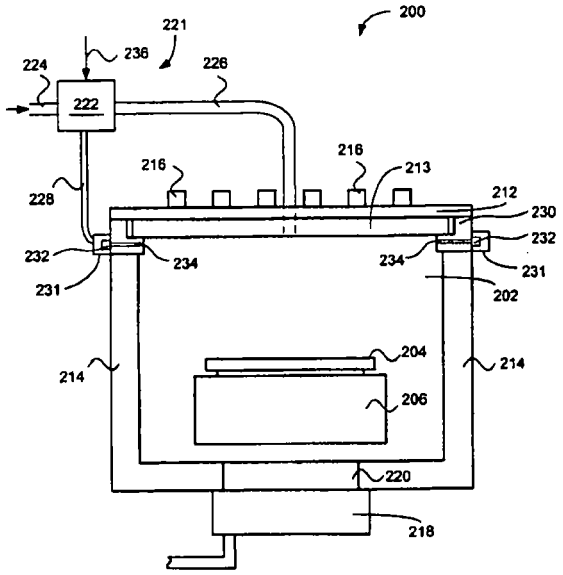
(54) Title: PLASMA PROCESSING SYSTEM WITH DYNAMIC GAS DISTRIBUTION CONTROL



(57) Abstract: A plasma processing system that includes a plasma processing chamber that provides enhanced control over an etch process is disclosed. The plasma processing chamber is connected to a gas flow system. The gas flow system can be employed to control the release of gases into different regions within the plasma processing chamber. In addition, the volume of the released gas, e.g., the flow rate of the gas, can be adjusted by a gas flow control mechanism. In this manner, both the position and the amount of the gas that is delivered to the plasma processing chamber can be controlled. The ability to adjust the position and the amount of gas that is released into the plasma processing chamber provides for a better control over the distribution of the neutral components. This in turn enhances control over the etching process.

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ACTION

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